

IN THE CLAIMS

What is claimed is:

- Sub C4
- 1 - 1. A method, comprising:
- 2 cleaning a plasma reactor chamber part, that may have a material
- 3 redistributed thereon by a reactive plasma process, by placing the chamber
- 4 part in a redistributed material solvent.
- Sub B
- 1 2. The method of claim 1, wherein:
- 2 the material includes photoresist polymers and the solvent includes
- 3 acetone.
- 1 3. The method of claim 1, wherein:
- 2 the chamber part comprises quartz.
- 1 - 4. The method of claim 1, wherein:
- 2 the chamber part is placed in the solvent for at least 6 hours.
- 1 - 5. The method of claim 1, further including:
- 2 cleaning the chamber part with a plasma that includes oxygen as a
- 3 source gas.

1 - 6. The method of claim 5, wherein:

2 the plasma is formed with a radio frequency (RF) power in the general
3 range of 500 to 1000 W.

1 - 7. The method of claim 5, further including:

2 rinsing the chamber part after cleaning with the solvent but before the
3 plasma cleaning.

1 - 8. The method of claim 1, further including:

2 ultrasonically cleaning the chamber part.) use

1 9. The method of claim 1, further including:

2 baking the chamber part at a temperature in the general range of 75-
3 150 °C.

1 ~ 10. A method of cleaning a plasma reactor chamber part, comprising:

2 plasma cleaning a chamber part, that may have having a material
3 redistributed on the chamber part by a reactive plasma process, with a plasma
4 having an etch selectivity between the chamber part and the redistributed
5 material that is greater than 1:100.

1 11. The method of claim 10, wherein:

2 the chamber part comprises quartz and the plasma includes oxygen as
3 a source gas.

1 ~ 12. The method of claim 10, wherein:

2 the plasma is formed with a radio frequency (RF) power in the general
3 range of 500 to 1000/W.

1 13. The method of claim 10, wherein:

2 the redistributed material includes photoresist polymers.

1 ~ 14. The method of claim 10, further including:

2 cleaning the chamber part with a solvent of the redistributed material.

Sub 1
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1 -15. A method of cleaning reactive plasma chamber parts, comprising the steps of:
2 applying an organic solvent to a surface of a chamber part; and
3 oxygen plasma cleaning the chamber part.

1 -16. The method of claim 15, wherein:
2 the organic solvent includes acetone.

Sub 1
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1 -17. The method of claim 15, further including:
2 rinsing the chamber part with de-ionized water after applying the
3 organic solvent.

1 -18. The method of claim 15, further including:
2 ultrasonically cleaning the chamber part after the oxygen plasma
3 cleaning.

1 -19. The method of claim 18, further including:
2 rinsing the chamber part with a liquid that evaporates at a lower
3 temperature than water after the ultrasonic cleaning.

1 20. The method of claim 15, further including:
2 baking the chamber part at a temperature greater than 80 °C for at
3 least 15 minutes.